

سيرة ذاتية

تاريخ الميلاد: 1950 / 21 / 01

محل الولادة: العراق / ذي قار

الجنسية: عراقي

اللغة: العربية والإنكليزية

العنوان الحالي: العراق بغداد

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التحصيل الأكاديمي

- بكالوريوس علوم فيزياء / جامعة بغداد / بغداد / 1974
- ماجستير فيزياء / أخشية رقيقة / جامعة بغداد / بغداد / 1977
- دكتوراه هندسة الكترونية / جامعة شفيلد / بريطانيا / 1984

المواد التي درستها

Electronics	
Mechanics	
Statistical Mechanics	
Quantum Mechanics	
Thermodynamics	
Semiconductors Devices	
Semiconductor Nano-Devices	
Laser Physics	

- الإلكترونيك
- الميكانيك
- الميكانيك الإحصائي
- الميكانيك الكم
- الترموداينمك
- نبائط أشباه الموصلات
- النبائط النانوية لأشباه الموصلات
- فيزياء الليزر

الاهتمامات البحثية

- نبائط أشباه الموصلات النانوية
- علم البرم الإلكتروني
- الخصائص الإلكترونية والبصرية لأشباه الموصلات

الوظائف التي شغلها

- تدريسي في جامعة بغداد لمدة 30 سنة متقدلاً بين:
- كلية التربية للبنات 1985 و حتى 1992
- كلية العلوم 1988 و حتى 1991
- كلية التربية ابن الهيثم 1992 و حتى 2015
- كلية الكوت الجامعة 2015 و حتى نهاية 2018
- كلية السلام الجامعة 2019 و حتى الان
-

البحوث المنشورة Research Publications

1. M. Cadim and T.S. Al-Bassam “Thickness Dependence of the Electrical Resistivity of Vacuum Evaporated Dysprosium Films”, *Thin Solid Films*, **41** (1977) L9 – L10.
2. M. Cadim and T.S. Al-Bassam “Hall Effect of Dysprosium Films”, *Thin Solid Films*, **41** (1977) L54 – L56.
3. M.C. Abdulrida and J. Allison “Thin Film Field Effect Transistors Incorporation Hydrogenated Amorphous Silicon Produced by R.F. Magnetron Sputtering”, *Thin Solid Films*, **102** (1983) L43 – L46.
4. H.L. Fernandez – Canque, M.C. Abdulrida and J. Allison “Comparative Methods for the Determination of the Gap States Density in Magnetron Sputtering Hydrogenated Amorphous Silicon”, *Thin Solid Films*, **110** (1983) pp. 241 – 250.
5. M.C. Abdulrida and J. Allison “Influence of Hydrogen on the Silicon Field Effect Transistors”, *Appl. Phys. Letts.*, **43** (8) (1983) 768.
6. A.H. Jaffar and M.C. Abdulrida “Characterization of Narrow Band Emission From Amorphous Chalcogenide Light Sources”, *Arab J. Phys.*, To be Published.
7. M.C. Abdulrida “Influence of States Density on the Performance of Hydrogenated Amorphous Silicon Thin Film Transistors” *Arab J.Phys.* (Submitted for Publication).
8. A.H. Musa, M.C. Abdulrida and M.A. Salim “Optical Properties of Tellurium / Aluminum Selective Absorber Surfaces”, Proceedings of International Renewable Energy Conference, Amman, 22 – 26 June, 1992.

9. M.C. Abdulrida, M.N. Makadsi and A.H. Shaban "Schottky Diode Solar Cells of D.C. Sputtered Hydrogenated Amorphous Silicon" Proceedings of the 1st Jordanian Mechanical Engineering Conference, Amman 25 – 28 June 1995.
10. M.C. Abdulrida, A.H. Jaffar and H.K. Rasheed, "Schottky Diode of D.C. Sputtered Hydrogenated Amorphous Silicon", J.Soc. Iraqi of Phys. And Math., **15** (2000) 99.
11. M.C. Abdulrida, B.A. Hassan and H.A.Hamed, "Magnetically Confined Arc Ion Source D.C. Sputtering of Hydrogenated Amorphous Silicon" To be Published in 4th International Conference in Physics of Condensed Matter, April 18th -22nd 2000.
12. M.C. Abdulrida, A.H. Jaffar and B.A. Al-Jazrawy, "Thermal Distribution in Laser Annealed Amorphous Silicon", Presented in the 42nd Week of Science, Conference of Laser Science and Application, University of Appolue, 2 – 4 Nov. 2002.
13. M.C. Abdulrida, W.O. Al-Khattab and B.A. Galib, "Schottky Barrier Depletion Width in Hydrogenated Amorphous Silicon", Ibn Al-Haitham Journal for Pure and Applied Sciences, Vol. 15 no.4 2002.
14. M.C. Abdulrida, B.A. Hassan and H.A. Hamed, "Optical Energy Gap of Magnetically Confined Ion Source D.C. Sputtered Hydrogenated Amorphous Silicon" Proceedings of the International Workshop on Physics and Technology of Thin Films, Editors: A.Z. Moshfegh et al., World Scientific, Tehran, Iran, 22Feb. – 6March 2003, pp. 355-362.
15. Z.T. Al-Dahan, M.C. Abdulrida and Z.T. Al-Ani "A Study of the Optical Properties of CuBr Thin Film", Ibn Al-Haitham Journal for Pure and Applied Sciences, Vol. **21**(3), 2008, pp. 112 – 128.
16. M.C. Abdulrida, H.I. Jaafer and E.T. Abdullah, Theoretical Study of Nanoscale Silicon Metal-Oxide-Semiconductor Field Effect Transistors For Two Different Single Gate

- Insulators”, Iraqi Journal of Physics, Vol. **5** (7), 2008, pp. 154 – 162.
17. S.M. Hassan, M. C. Abdulrida and H.I. Jafaar, “Optical Properties of Prepared Pure and Doped Polyanilinne Salt”, Proceeding of 3rd Conference of the College of Science, University of Baghdad 24th to 26th March 2009, Baghdad. pp. 2335 – 2339.
18. R.H. Risan, A.H. Shaban and M.C. Abdulrida, “Resonance Tunneling Through GaN/AlGaN Superlattice System”, Iraqi Journal of Physics, Vol. **7** (8), 2009, pp. 63 – 68.
19. R.A. Al-Wardy, M.C. Abdulrida and I.R. Agool, “Resonance Tunneling in Amorphous Si/Si_{1-x}Ge_x Quantum Wells Superlattice”, Journal of Kufa – Physics a Special Issue for Kufa’s First Conference for Physics, 6th - 7th October 2010, pp. 621 – 629.
20. S.M. Hassan, H.I. Jafaar and M.C. Abdulrida, ”D.C. Conductivity of Prepared Pure and Doped Polyaniline Salt”, Journal of Kufa – Physics a Special Issue for Kufa’s First Conference for Physics, 6th - 7th October 2010, pp. 8 – 15.
- 21 The influence of confinements on the photon flux spectra in amorphous silicon quantum dots, MC Abdulrida, NM Abdul-Ameer, SM Abdul-Hakeem, Turkish Journal of Physics 36 (2), 197-205
- 23 The Effect of Temperature width on Dielectric Constant of Vanadium Dioxide, Nidhal M. Abdul-Ameer, Imad H. Khaleel, Shaymaa Qasim Abdul Hasan, Moafak C. Abdulrida Key Engineering Materials 886, pp 108-116
- 24 Photoluminescence Spectra From The Direct Energy Gap of a-SiQDs, NM Abdul-Ameer, MC Abdulrida, SM Abdul-Hakeem Journal of Physics: Conference Series 1003 (1), 012105
- 25 Size Dependence of the Dielectric Susceptibility of NanoSolid Amorphous Silicon, NMAA Moafak Cadim Abdulrida, Hussein K. Mejbel, First International Scientific Conference / part 2, 94-101.

- 26 Dielectric Reduction of Nanometric Amorphous Silicon, MCA
Hussein K. Mejbel, The Scientific Journal of Thi-Qar
- 27 Influence of Injection Current on the Internal Quantum Efficiency
of a-Si Quantum Dot's Light Emitting Diodes
MCAWK Jameel
Al-Kut University College Journal 1 (1), 10 - 18
- 28 Temperature and Recombination Lifetime Effects on Amorphous
Silicon Quantum Dot's Light Emitting Diodes, WKJ MC
Abdulrida Advances in Physics Theories and Applications 48,
23 - 27
- 29 The dependence of resonant tunneling transmission coefficient
on well width and barriers number of GaN/Al_{0.3}Ga_{0.7}N
nanostructured system, MC Abdulrida, Iraqi Journal of Physics
(IJP) 11 (21), 108-115
- 30 Theoretical Nanoscience for Laser and Optoelectronic Devices,
Department of physics, College of Education (A Simple
Theoretical Model for Thermoelectric Cooling of Bi₂Te₃ and
MC Abdulrida, I Al-Haitham, Al-Mustansiriyah Journal of
Science 23 (4)

روابط الحسابات العلمية

[Google Scholar](#)

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